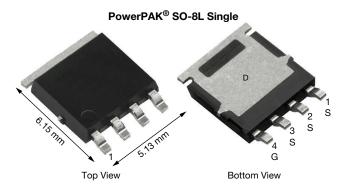
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Automotive P-Channel 40 V (D-S) 175 °C MOSFET



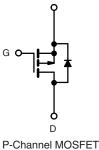
PRODUCT SUMMARY	
V _{DS} (V)	-40
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0070
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0100
I _D (A)	-60
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



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P-Channel WOSFET

ABSOLUTE MAXIMUM RATINGS (T_C	= 25 °C, unles	s otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-40	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	$T_C = 25 \ ^\circ C \ ^a$	L	-60	
Continuous drain current	T _C = 125 °C	۱ _D	-42	
Continuous source current (diode conduction) ^a		ا _S	-60	А
Pulsed drain current ^b		I _{DM}	-150	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-41	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	84	mJ
Maximum power dissipation ^b	T _C = 25 °C	PD	68	W
T _C	T _C = 125 °C	FD	22	vv
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) d, e)		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	68	°C/W
Junction-to-case (drain)		R _{thJC}	2.2	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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SPECIFICATIONS ($T_C = 25 \ ^{\circ}C$,	unless otherw	vise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μA	-40	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -40 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA
		$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 V$	-30	-	-	Α
		$V_{GS} = -10 V$	I _D = -10 A	-	0.0058	0.0070	
Drain course on state registered a	P	V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0106	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0126	Ω
		V _{GS} = -4.5 V	I _D = -6 A	-	0.0083	0.0100	1
Forward transconductance b	9 _{fs}	V _{DS} =	-15 V, I _D = -10 A	-	54	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	8400	11 000	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	620	850	pF
Reverse transfer capacitance	C _{rss}			-	510	700	
Total gate charge ^c	Qg			-	170	260	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -10 V$	$V_{DS} = -20 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	24	-	nC
Gate-drain charge ^c	Q _{gd}			-	35	-	
Gate resistance	Rg		f = 1 MHz	0.50	1.08	1.70	Ω
Turn-on delay time ^c	t _{d(on)}			-	23	35	
Rise time ^c	t _r	V _{DD}	= -20 V, R _L = 4 Ω	-	18	30	
Turn-off delay time ^c	t _{d(off)}	I _D ≅ -5 A, '	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	75	120	ns
Fall time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Char	acteristics ^b	•				•	
Pulsed current ^a	I _{SM}			-	-	-150	Α
Forward voltage	V _{SD}	I _F =	-10 A, V _{GS} = 0 V	-	-0.76	-1.2	V
Body diode reverse recovery time	t _{rr}			-	39	90	ns
Body diode reverse recovery charge	Q _{rr}			-	45	100	nC
Reverse recovery fall time	ta	I _F = -10	A, dl/dt = 100 A/µs	-	22	-	
Reverse recovery rise time	t _b	1		-	19	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}				-2.3	-	А

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

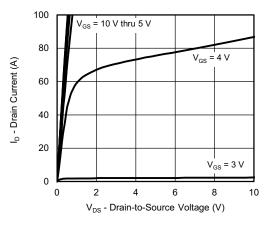
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

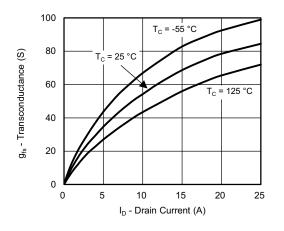
2



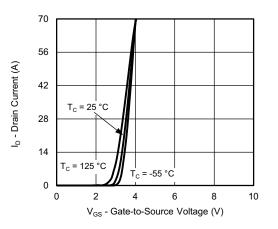
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



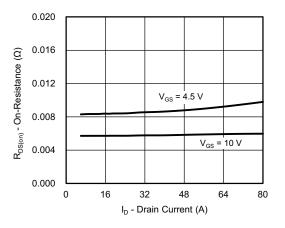
Output Characteristics



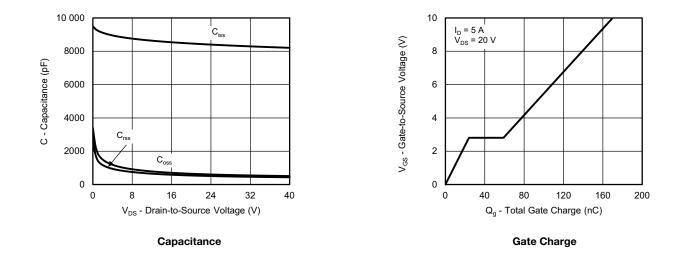
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



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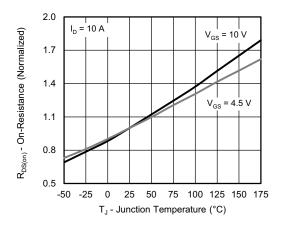
3

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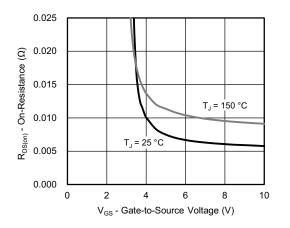
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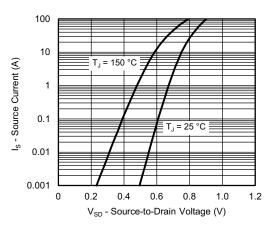
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



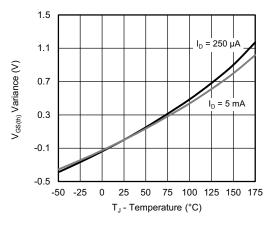
On-Resistance vs. Junction Temperature



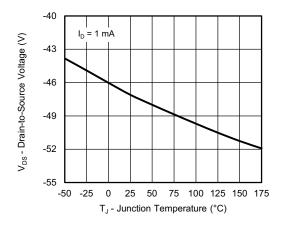
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage

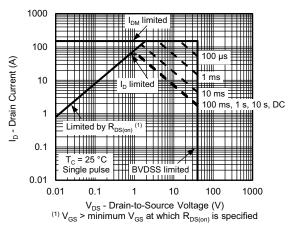


Drain-Source Breakdown vs. Junction Temperature

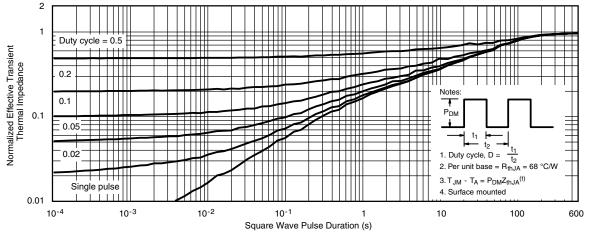
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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

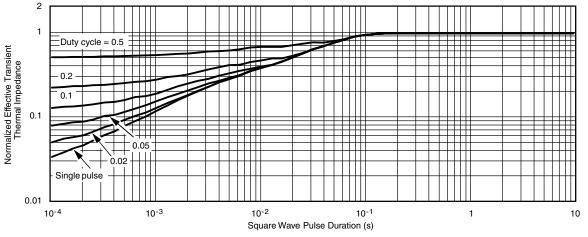


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THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77707.

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Package Information



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DIM.		MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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